

FFH50US60S

50A, 600V Stealth™ Diode

General Description

The FFH50US60S is a StealthTM diode optimized for low loss performance in output rectification. The StealthTM family exhibits low reverse recovery current ($I_{RM(REC)}$), low V_F and soft recovery under typical operating conditions.

This device is intended for use as an output rectification diode in Telecom power supplies and other power switching applications. Lower V_F and $I_{RM(REC)}$ reduces diode losses.

Formerly developmental type TA49468.

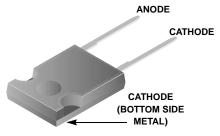
Features

•	Soft Recovery $t_b/t_a > 1.5$
•	Fast Recovery
•	Operating Temperature 175°C
•	Reverse Voltage 600V
•	Avalanche Energy Rated 20mJ

Applications

- Switch Mode Power Supplies
- Power Factor Correction
- · Uninterruptible Power Supplies
- Motor Drives
- Welders

Package Symbol JEDEC STYLE 2 LEAD TO-247





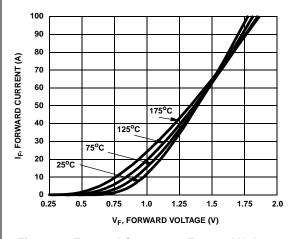
Device Maximum Ratings $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{RRM}	Repetitive Peak Reverse Voltage	600	V
V _{RWM}	Working Peak Reverse Voltage	600	V
V _R	DC Blocking Voltage	600	V
I _{F(AV)}	Average Rectified Forward Current (T _C = 120°C)	50	Α
I _{FRM}	Repetitive Peak Surge Current (20kHz Square Wave)	100	Α
I _{FSM}	Nonrepetitive Peak Surge Current (Halfwave 1 Phase 60Hz)	500	Α
P _D	Power Dissipation	200	W
E _{AVL}	Avalanche Energy (1A, 40mH)	20	mJ
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to 175	°C
TL	Maximum Temperature for Soldering		
T_{PKG}	Leads at 0.063in (1.6mm) from Case for 10s	300	°C
	Package Body for 10s, See Application Note AN-7528	260	°C

CAUTION: Stresses above those listed in "Device Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Device	Marking	Device	Package Tape Width				Quan	tity
50U	S60S	9 ,		N/A			30	
Electric	al Cha	racteristics τ _c = 25°C	unless otherwis	e noted				
Symbol	mbol Parameter		Test Conditions		Min	Тур	Max	Units
Off State	Charact	eristics	•					
I _R	Instantaneous Reverse Current		V _R = 600V	T _C = 25°C	-	-	100	μA
1				T _C = 125°C	-	-	1	mA
On State	Charact	eristics				•		
V _F	Instantaneous Forward Voltage		I _F = 50A	T _C = 25°C	-	1.38	1.54	V
		ŭ	'	T _C = 125°C	-	1.37	1.53	V
	Charact		TV -40V I - (2 Λ Ι		110		nE
СЈ	Junction C	Sapacitance	$V_R = 10V, I_F = 0A$		-	110	-	pF
Switchin	g Charac	cteristics						
t _{rr}	Reverse Recovery Time $I_F = 1A$, $dI_F/dt = 100A/\mu s$, $V_R = 15V$		-	47	80	ns		
			$I_F = 50A$, $dI_F/dt = 100A/\mu s$, $V_R = 100A/\mu s$		-	75	124	ns
t _{rr}	Reverse R	ecovery Time	I _F = 50A,		-	113	-	ns
I _{RM(REC)} Maximum Reverse Recovery Current		$dI_F/dt = 200A/\mu s,$		-	9.6	-	Α	
Q _{RR}			$V_{R} = 390V, I_{C}$	$V_R = 390V, T_C = 25^{\circ}C$		0.9	-	μC
t _{rr}	Reverse R	ecovery Time	I _F = 50A,			235	-	ns
S	Softness F	actor (t _b /t _a)	$dI_F/dt = 200A/\mu s$,			1.5	-	-
I _{RM(REC)} Maximum Rev		Reverse Recovery Current	$V_R = 390V,$ $T_C = 125^{\circ}C$		-	15	-	Α
Q_{RR}	Reverse R	ecovered Charge	- 1 _C = 125 C			2.3	-	μC
t _{rr}	Reverse R	ecovery Time	I _F = 50A, dI _F /dt = 1000A/μs, V _R = 390V, T _C = 125°C			110	-	ns
S	Softness F	actor (t _b /t _a)				0.8	-	-
I _{RM(REC)}	Maximum	Reverse Recovery Current				46	-	Α
Q _{RR}	Reverse R	ecovered Charge				3.1	-	μC
dl _M /dt	Maximum	di/dt during t _b				1000	-	A/µs
Thermal	Characte	eristics						
$R_{\theta JC}$	Thermal R	esistance Junction to Case			-	-	0.75	°C/W
R _{θJA}	Thormal D	Posistance Junction to Ambion	mbient TO-247				30	°C/W

Typical Performance Curves



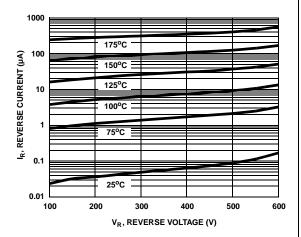
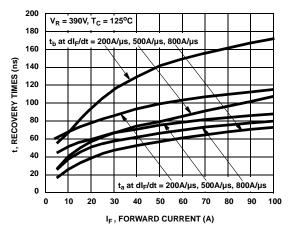


Figure 1. Forward Current vs Forward Voltage

Figure 2. Reverse Current vs Reverse Voltage



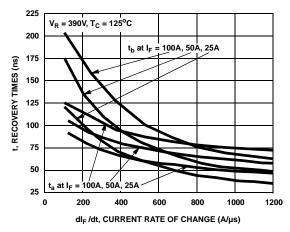
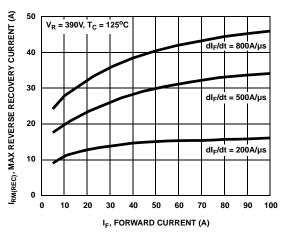


Figure 3. t_a and t_b Curves vs Forward Current

Figure 4. t_a and t_b Curves vs dI_F/dt



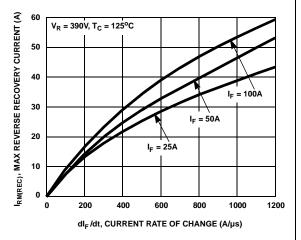


Figure 5. Maximum Reverse Recovery Current vs Forward Current

Figure 6. Maximum Reverse Recovery Current vs dI_F/dt

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Typical Performance Curves (Continued)

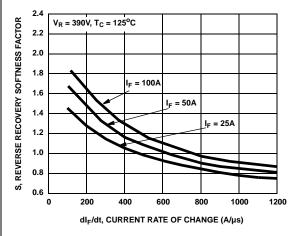


Figure 7. Reverse Recovery Softness Factor vs $\mathrm{dI_F/dt}$

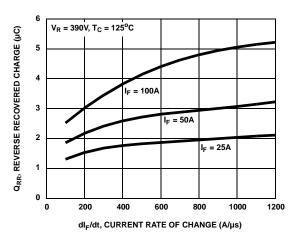


Figure 8. Reverse Recovery Charge vs dl_F/dt

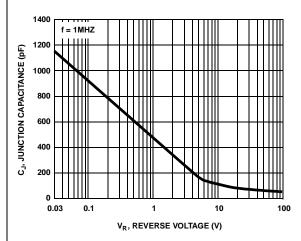


Figure 9. Junction Capacitance vs Reverse Voltage

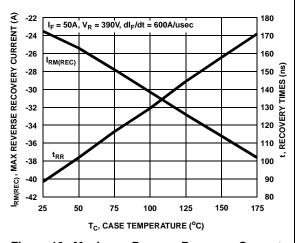


Figure 10. Maximum Reverse Recovery Current and t_{rr} vs Case Temperature

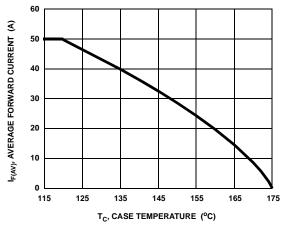


Figure 11. DC CURRENT DERATING CURVE

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Typical Performance Curves (Continued)

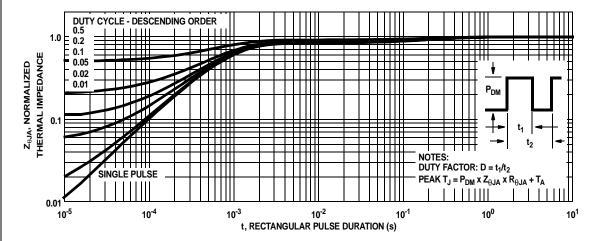
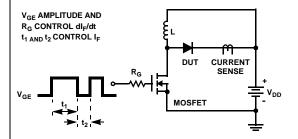


Figure 12. Normalized Maximum Transient Thermal Impedance

Test Circuit and Waveforms



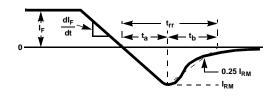
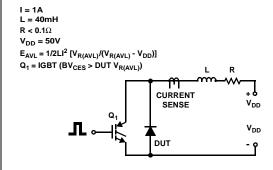


Figure 13. t_{rr} Test Circuit

Figure 14. t_{rr} Waveforms and Definitions



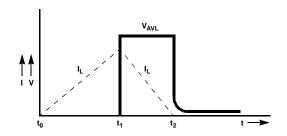


Figure 15. Avalanche Energy Test Circuit

Figure 16. Avalanche Current and Voltage Waveforms

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